

# SEMICONDUCTOR TECHNICAL DATA

### 2N5551S

#### EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION. HIGH VOLTAGE APPLICATION.

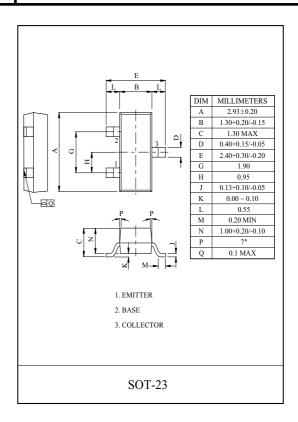
#### **FEATURES**

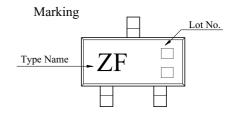
- · High Collector Breakdwon Voltage
  - $: V_{CBO} = 180V, V_{CEO} = 160V$
- · Low Leakage Current.
  - :  $I_{CBO}$ =50nA(Max.)  $V_{CB}$ =120V
- · Low Saturation Voltage
  - :  $V_{CE(sat)}$ =0.2V(Max.)  $I_{C}$ =50mA,  $I_{B}$ =5mA
- · Low Noise: NF=8dB (Max.)

#### MAXIMUM RATING (Ta=25 )

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V <sub>CBO</sub>	180	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V	
Emitter-Base Voltage	$V_{EBO}$	6	V	
Collector Current	$I_{C}$	600	mA	
Base Current	$I_{\mathrm{B}}$	100	mA	
Collector Power Dissipation	P <sub>C</sub> *	350	mW	
Junction Temperature	$T_{j}$	150		
Storage Temperature Range	$T_{stg}$	-55 150		

Note : \* Package Mounted On 99.5% Alumina  $10 \times 8 \times 0.6$ mm)





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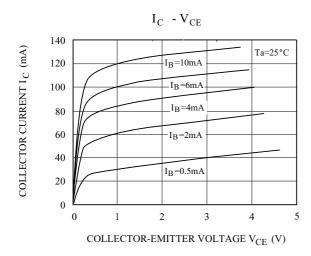
## ELECTRICAL CHARACTERISTICS (Ta=25 )

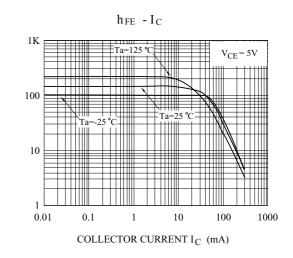
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=120V, I_{E}=0$	-	-	50	nA
		V <sub>CB</sub> =120V, I <sub>E</sub> =0, Ta=100	-	-	50	μΑ
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=4V$ , $I_{C}=0$	-	-	50	nA
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	$I_{C}=0.1 \text{mA}, I_{E}=0$	180	-	-	V
Collector-Emitter * Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_C=1$ mA, $I_B=0$	160	-	-	V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	$I_{\rm E} = 10 \mu \text{A}, \ I_{\rm C} = 0$	6	-	-	V
DC Current Gain *	h <sub>FE</sub> (1)	$V_{CE}=5V$ , $I_{C}=1mA$	80	-	-	-
	h <sub>FE</sub> (2)	$V_{CE}=5V$ , $I_{C}=10mA$	80	-	250	
	h <sub>FE</sub> (3)	$V_{CE}=5V$ , $I_{C}=50$ mA	30	-	-	
Collector-Emitter *	V <sub>CE(sat)</sub> 1	$I_C=10\text{mA}, I_B=1\text{mA}$	-	-	0.15	V
Saturation Voltage	V <sub>CE(sat)</sub> 2	$I_C=50\text{mA}, I_B=5\text{mA}$	-	-	0.2	v
Base-Emitter *	V <sub>BE(sat)</sub> 1	$I_C=10\text{mA}, I_B=1\text{mA}$	-	-	1.0	V
Saturation Voltage	V <sub>BE(sat)</sub> 2	$I_C=50\text{mA}, I_B=5\text{mA}$	-	-	1.0	v
Transition Frequency	$f_T$	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz	100	-	300	MHz
Collector Output Capacitance	C <sub>ob</sub>	$V_{CB}=10V$ , $I_{E}=0$ , $f=1MHz$	-	-	6	pF
Input Capacitance	C <sub>ib</sub>	$V_{BE}$ =0.5V, $I_{C}$ =0, f=1MHz	-	-	20	pF
Small-Signal Current Gain	h <sub>fe</sub>	$V_{CE}=10V$ , $I_{C}=1mA$ , $f=1kHz$	50	-	200	-
Noise Figure	NF	V <sub>CE</sub> =5V, I <sub>C</sub> =250μA Rg=1k , f=10Hz 15.7kHz	-	-	8	dB

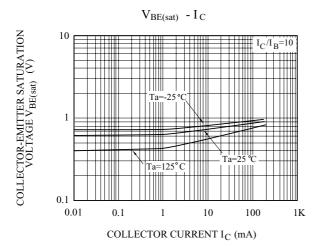
<sup>\*</sup> Pulse Test : Pulse Width 300 μs, Duty Cycle 2%.

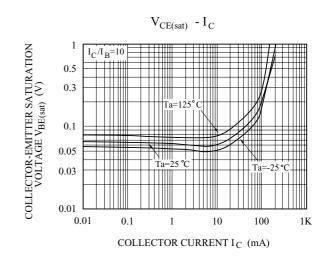
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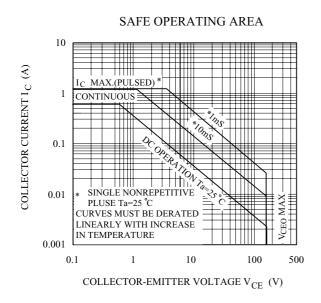
DC CURRENT GAIN hFE











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